**Amendments to the Claims:**

Please cancel claim 116. Following is a complete listing of the claims pending in the application, as amended:

1-2. (Cancelled)

3. (Previously presented) A method for removing an electrically conductive material from a microelectronic substrate, comprising:

selecting first and second conductive electrodes to have a combined surface area facing toward a surface of the microelectronic substrate that is less than the area of the surface of the microelectronic substrate;

positioning the first conductive electrode proximate to the microelectronic substrate;

positioning the second conductive electrode proximate to the microelectronic substrate and spaced apart from the first conductive electrode;

removing the conductive material from the microelectronic substrate by passing a varying current through the first and second electrodes while the first and second electrodes are spaced apart from the conductive material of the microelectronic substrate; and

moving at least one of the microelectronic substrate and the electrodes relative to the other while passing the current through the electrodes.

4-5. (Cancelled)

6. (Previously presented) A method for removing an electrically conductive material from a microelectronic substrate, comprising:

positioning a first conductive electrode proximate to the microelectronic substrate;

positioning a second conductive electrode proximate to the microelectronic substrate and spaced apart from the first conductive electrode;

removing the conductive material from the microelectronic substrate by passing a varying current through the first and second electrodes while the first and second electrodes are spaced apart from the conductive material of the microelectronic substrate; and

varying an amplitude and/or polarity of the current at a first frequency and superimposing on the first frequency an amplitude variation having a second frequency less than the first frequency.

7. (Cancelled)

8. (Previously presented) A method for removing an electrically conductive material from a microelectronic substrate, comprising:

positioning a first conductive electrode proximate to the microelectronic substrate;

positioning a second conductive electrode proximate to the microelectronic substrate and spaced apart from the first conductive electrode, the first and second electrodes defining a first electrode pair;

removing a first portion of the conductive material from the microelectronic substrate by passing a varying current through the first and second electrodes while the first and second electrodes are spaced apart from the conductive material of the microelectronic substrate;

positioning a second electrode pair proximate to the microelectronic substrate; and

applying a varying current to the second electrode pair to remove a second portion of conductive material from the microelectronic substrate.

9-31. (Cancelled)

32. (Previously presented) A method for forming a planarizing medium, comprising:

forming a planarizing pad body having a planarizing surface to engage a surface of a microelectronic substrate;

disposing a first electrode at least adjacent to the planarizing pad body and spaced apart from the planarizing surface with the first electrode coupleable to a source of varying current;

disposing a second electrode at least adjacent to the planarizing pad body with the second electrode spaced apart from the first electrode;

disposing a dielectric material between the first and second electrodes; and

disposing a dielectric film between the planarizing surface and the electrodes.

33-36. (Cancelled)

37. (Original) A method for removing an electrically conductive material from a microelectronic substrate, comprising:

positioning a first conductive electrode proximate to a first portion of the microelectronic substrate;

positioning a second conductive electrode proximate to the first portion of microelectronic substrate and spaced apart from the first conductive electrode, the first and second electrodes defining an electrode pair;

removing the conductive material from the first portion of the microelectronic substrate by passing a varying current through the first and second electrodes while the first and second electrodes are spaced apart from the conductive material of the microelectronic substrate;

moving at least one of the microelectronic substrate and the electrode pair relative to the other to align a second portion of the microelectronic substrate with the electrode pair; and

removing the conductive material from the second portion of the microelectronic substrate by applying a varying current to at least one of the first and

second electrodes while the first and second electrodes are spaced apart from the conductive material of the microelectronic substrate.

38. (Original) The method of claim 37, further comprising:

directing a first flow of electrolyte only to the first portion of the microelectronic substrate when the electrode pair is proximate to the first potion; and

directing a second flow of electrolyte only to the second portion of the microelectronic substrate when the electrode pair is proximate to the second potion.

39-42. (Cancelled)

43. (Original) A method for removing an electrically conductive material from a microelectronic substrate, comprising:

positioning a first conductive electrode at least proximate to a first portion of the microelectronic substrate;

positioning a second conductive electrode at least proximate to the first portion of the microelectronic substrate and spaced apart from the first conductive electrode, the first and second electrodes defining a first electrode pair;

positioning a second electrode pair at least proximate to a second portion of the microelectronic substrate, the second electrode pair including a third electrode and a fourth electrode spaced apart from the third electrode; and

removing the conductive material from the microelectronic substrate by passing a first varying current through the first and second electrodes and passing a second varying current through the third and fourth electrodes.

44. (Original) The method of claim 43, further comprising spacing the first and second electrodes apart from the microelectronic substrate while applying the first varying current.

45. (Original) The method of claim 43, further comprising spacing the first electrode pair a first distance from a surface of the microelectronic substrate and spacing the second electrode pair a second distance from the surface of the microelectronic substrate with the first distance greater than the second distance.

46. (Original) The method of claim 43, further comprising:

spacing the first and second electrode pair apart from each other by a first distance;

spacing a third and fourth electrode pair apart from each other by a second distance greater than the first distance, with each of the third and fourth electrode pairs including two spaced apart electrodes;

aligning the third electrode pair with a third portion of the microelectronic substrate and aligning the fourth electrode pair with a fourth portion of the microelectronic substrate; and

removing the conductive material from the third and fourth portions of the microelectronic substrate by passing a third varying current through the third electrode pair and passing a fourth varying current through the fourth electrode pair.

47. (Original) The method of claim 43 wherein the first varying current is approximately identical to the second varying current.

48. (Original) The method of claim 43 wherein an amplitude of the first varying current is greater than an amplitude of the second varying current.

49-52. (Cancelled)

53. (Previously presented) An apparatus for removing conductive material from a microelectronic substrate, comprising:

a support member having at least one engaging surface to support the microelectronic substrate;

a first electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member;

a second electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member, the second electrode being spaced apart from the first electrode; and

a current source configured to vary an amplitude of the current at a first frequency, the current source including an amplitude modulator to superimpose on the first frequency an amplitude and/or polarity variation having a second frequency less than the first frequency, wherein at least one of the first and second electrodes is coupleable to the current source.

54. (Cancelled)

55. (Previously presented) An apparatus for removing conductive material from a microelectronic substrate, comprising:

a support member having at least one engaging surface to support the microelectronic substrate;

a first electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member;

a second electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member, the second electrode being spaced apart from the first electrode, the first and second electrodes defining a first electrode pair, at least one of the first and second electrodes being coupleable to a source of varying current;

a third electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member; and

a fourth electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member, the fourth electrode being spaced apart from the third electrode, at least one of the third and fourth electrodes being coupleable to a source of varying current.

56-67. (Cancelled)

68. (Previously presented) An apparatus for removing a conductive material from a microelectronic substrate, comprising:

a carrier having at least one engaging surface to support a microelectronic substrate;

a polishing pad proximate to the carrier and having a polishing surface to engage the microelectronic substrate, at least one of the polishing pad and the carrier being movable relative to the other;

a first electrode proximate to the polishing surface; and

a second electrode proximate to the polishing surface and spaced apart from the first electrode; and

a current source configured to vary an amplitude of the current at a first frequency, further wherein the current source includes an amplitude modulator to superimpose on the first frequency an amplitude and/or polarity variation having a second frequency less than the first frequency, and wherein at least one of the first and second electrodes is coupleable to the current source.

69. (Previously presented) An apparatus for removing a conductive material from a microelectronic substrate, comprising:

a carrier having at least one engaging surface to support a microelectronic substrate;

a polishing pad proximate to the carrier and having a polishing surface to engage the microelectronic substrate, at least one of the polishing pad and the carrier being movable relative to the other;

a first electrode proximate to the polishing surface;

a second electrode proximate to the polishing surface and spaced apart from the first electrode, at least one of the first and second electrodes being coupleable to a source of varying electrical current, the first and second electrodes defining a first electrode pair;

a third electrode spaced apart from the carrier and from the microelectronic substrate when the microelectronic substrate is supported by the carrier; and

a fourth electrode spaced apart from the carrier and from the microelectronic substrate when the microelectronic substrate is supported by the carrier, the fourth electrode being spaced apart from the third electrode, at least one of the third and fourth electrodes being coupleable to a source of varying current.

70-75. (Cancelled)

76. (Original) An apparatus for removing an electrically conductive material from a microelectronic substrate, comprising:

a support member having at least one engaging surface to support the microelectronic substrate;

first and second conductive electrodes spaced apart from each other and defining a first electrode pair, the first electrode pair being at least proximate to the microelectronic substrate when the microelectronic substrate is supported by the support member, at least one of the first and second electrodes being coupleable to a source of varying current; and

third and fourth conductive electrodes spaced apart from each other and defining a second electrode pair spaced apart from the first electrode pair, the second electrode pair being at least proximate to the microelectronic

substrate when the microelectronic substrate is supported by the support member, at least one of the third and fourth electrodes being coupleable to a source of varying current.

77. (Original) The apparatus of claim 76 wherein the first and second electrodes are positioned to be spaced apart from the microelectronic substrate when the microelectronic substrate is supported by the support member.

78. (Original) The apparatus of claim 76 wherein the first electrode pair is positioned a first distance from a surface of the microelectronic substrate and the second electrode pair is positioned a second distance from the surface of the microelectronic substrate when the support member supports the microelectronic substrate, with the first distance greater than the second distance.

79. (Original) The apparatus of claim 76, further comprising a third and fourth electrode pair, the third and fourth electrode pairs each including two spaced apart electrodes, the first and second electrode pair spaced apart from each other by a first distance and the third and fourth electrode pair spaced apart from each other by a second distance greater than the first distance.

80. (Original) The apparatus of claim 76 wherein an amplitude of varying current supplied to the first and second electrodes is different than an amplitude of varying current supplied to the third and fourth electrodes.

81. (Original) The apparatus of claim 76 wherein a frequency of varying current supplied to the first and second electrodes is higher than a frequency of varying current supplied to the third and fourth electrodes.

82. (Previously presented) The method of claim 3, further comprising disposing a liquid and/or gel electrolyte between the electrodes and the microelectronic substrate.

83. (Previously presented) The method of claim 3, further comprising controlling a rate at which the conductive material is removed from the microelectronic substrate by controlling a distance between at least one of the electrodes and the microelectronic substrate.

84. (Previously presented) The method of claim 3, further comprising controlling a rate at which the conductive material is removed from the microelectronic substrate by spacing a first portion of the first electrode a first distance away from a first region of the microelectronic substrate and spacing a second portion of the first electrode a second distance away from a second region of the microelectronic substrate with the first distance being different than the second distance.

85. (Previously presented) The method of claim 3, further comprising:
at least partially immersing the microelectronic substrate in a liquid electrolyte;
moving portions of the electrically conductive material from the microelectronic substrate to the liquid electrolyte; and
removing the portions from the liquid electrolyte.

86. (Previously presented) The method of claim 3, further comprising:
disposing a first quantity of an electrolyte between the conductive material and the electrodes only in a first region of the microelectronic substrate immediately proximate to the electrodes;
moving the microelectronic substrate and/or the electrodes to align a second region of the microelectronic substrate with the electrodes; and
disposing a second quantity of the electrolyte between the conductive material and the electrodes only in the second region of the microelectronic substrate.

87. (Previously presented) The method of claim 3, further comprising:
disposing a first electrolyte adjacent to the first electrode;

disposing a second electrolyte different than the first electrolyte adjacent to the conductive material of the microelectronic substrate; and

at least restricting movement of the second electrolyte toward the first electrode.

88. (Previously presented) The method of claim 3, further comprising:

generating a signal corresponding to a rate at which the conductive material is removed from the microelectronic substrate and/or an amount of conductive material remaining on the microelectronic substrate; and

controlling an interaction between the microelectronic substrate and the electrodes based on the signal.

89. (Previously presented) The method of claim 6, further comprising:

disposing a first quantity of an electrolyte between the conductive material and the electrodes only in a first region of the microelectronic substrate immediately proximate to the electrodes;

moving the microelectronic substrate and/or the electrodes to align a second region of the microelectronic substrate with the electrodes; and

disposing a second quantity of the electrolyte between the conductive material and the electrodes only in the second region of the microelectronic substrate.

90. (Previously presented) The method of claim 6, further comprising:

disposing a first electrolyte adjacent to the first electrode;

disposing a second electrolyte different than the first electrolyte adjacent to the conductive material of the microelectronic substrate; and

at least restricting movement of the second electrolyte toward the first electrode.

91. (Previously presented) The method of claim 90 wherein at least restricting motion of the second electrolyte includes disposing a permeable membrane between the one electrode and the microelectronic substrate and passing the first electrolyte through the membrane.

92. (Previously presented) The method of claim 90, further comprising selecting the first electrolyte to include sodium chloride, potassium chloride, and/or or copper sulfate.

93. (Previously presented) The method of claim 90, further comprising selecting the second electrolyte to include hydrochloric acid.

94. (Previously presented) An apparatus for removing conductive material from a microelectronic substrate, comprising:

an electrolyte vessel configured to support a liquid electrolyte;

a support member having at least one engaging surface to support the microelectronic substrate, the support member being positioned relative to the electrolyte vessel to support the microelectronic substrate within the vessel;

a first electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member;

a second electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member, the second electrode being spaced apart from the first electrode, the first and second electrodes being positioned to pass electrical current through a current path that includes the first and second electrodes and the microelectronic substrate when the microelectronic substrate is supported by the support member; and

a current source that includes a single phase or a multi-phase alternating current supply, wherein at least one of the first and second electrodes is coupleable to the current source.

95. (Previously presented) An apparatus for removing conductive material from a microelectronic substrate, comprising:

a support member having at least one engaging surface to support the microelectronic substrate;

a first electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member;

a second electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member, the second electrode being spaced apart from the first electrode, the first and second electrodes being positioned to pass electrical current through a current path that includes the first and second electrodes and the microelectronic substrate when the microelectronic substrate is supported by the support member;

a current source that includes a single phase or a multi-phase alternating current supply, wherein at least one of the first and second electrodes is coupleable to the current source; and

wherein the microelectronic substrate has a surface facing toward the first and second electrodes, and further wherein the first and second electrodes have a combined surface area facing toward the surface of the microelectronic substrate that is approximately equal to the surface area of the microelectronic substrate.

96-97. (Cancelled)

98. (Previously presented) An apparatus for removing conductive material from a microelectronic substrate, comprising:

a support member having at least one engaging surface to support the microelectronic substrate;

a first electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member;

a second electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member, the second electrode being spaced apart from the first electrode, the first and second electrodes being positioned to pass electrical current through a current path that includes the first and second electrodes and the microelectronic substrate when the microelectronic substrate is supported by the support member;

a current source that includes a single phase or a multi-phase alternating current supply, wherein at least one of the first and second electrodes is coupleable to the current source; and

wherein at least one of the first electrode and the support member is movable relative to the other and the first electrode includes a first surface portion and a second surface portion, the first and second surface portions facing the microelectronic substrate when the microelectronic substrate is supported by the support member, the first portion being positioned further from the microelectronic substrate than the second portion when a first region of the microelectronic substrate opposite the first portion has a slower velocity relative to the first electrode than does a second region of the microelectronic substrate opposite the second portion of the first electrode.

99. (Previously presented) An apparatus for removing conductive material from a microelectronic substrate, comprising:

a support member having at least one engaging surface to support the microelectronic substrate;

a first electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member;

a second electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member, the second electrode being spaced apart from the first electrode, the first and second electrodes being positioned to pass electrical current through a current path that includes the first and second electrodes and the microelectronic substrate when the microelectronic substrate is supported by the support member;

a current source that includes a single phase or a multi-phase alternating current supply, wherein at least one of the first and second electrodes is coupleable to the current source; and

a sensor positioned at least proximate to the support member to detect a rate at which the conductive material is removed from the microelectronic substrate and/or an amount of conductive material remaining on the microelectronic substrate.

100. (Previously presented) The apparatus of claim 99 wherein the sensor is coupled to the current source and/or at least one of the electrodes to control an electrical potential imparted to the microelectronic substrate when the microelectronic substrate is supported by the support member.

101. (Previously presented) The method of claim 68, further comprising:

a sensor positioned at least proximate to the support member to detect a rate at which the conductive material is removed from the microelectronic substrate and/or an amount of conductive material remaining on the microelectronic substrate, the sensor being coupled to the current source and/or at least one of the electrodes to control an electrical potential imparted to the microelectronic substrate when the microelectronic substrate is supported by the carrier.

102. (Previously presented) An apparatus for removing conductive material from a microelectronic substrate, comprising:

a support member having at least one engaging surface to support the microelectronic substrate;

a first electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member;

a second electrode spaced apart from the support member and from the microelectronic substrate when the microelectronic substrate is supported by the support member, the second electrode being spaced apart from the first electrode, the first and second electrodes being positioned to pass electrical current through a current path that includes the first and second electrodes and the microelectronic substrate when the microelectronic substrate is supported by the support member;

a current source that includes a single phase or a multi-phase alternating current supply, wherein at least one of the first and second electrodes is coupleable to the current source; and

an electrolyte flow restrictor positioned between the support member and at least one of the conductive electrodes to at least restrict a flow of an electrolyte toward at least one of the first and second electrodes.

103. (Previously presented) The apparatus of claim 102, further comprising:

a first electrolyte adjacent to the microelectronic substrate and selected from sodium chloride, potassium chloride and copper sulfate; and

a second electrolyte adjacent to at least one of the electrodes and selected to include hydrochloric acid.

104. (Previously presented) The apparatus of claim 102 wherein the flow restrictor includes a permeable membrane.

105. (Previously presented) The method of claim 3 wherein removing the conductive material includes contacting the microelectronic substrate with a polishing pad while moving at least one of the microelectronic substrate and the electrodes relative to the other.

106. (Previously presented) The method of claim 37, further comprising disposing a liquid and/or gel electrolyte between the electrodes and the microelectronic substrate.

107. (Previously presented) The method of claim 37, further comprising controlling a rate at which the conductive material is removed from the microelectronic substrate by controlling a distance between at least one of the electrodes and the microelectronic substrate.

108. (Previously presented) The method of claim 37, further comprising controlling a rate at which the conductive material is removed from the microelectronic substrate by spacing a first part of the first electrode a first distance away from a first region of the microelectronic substrate and spacing a second part of the first electrode a second distance away from a second region of the microelectronic substrate with the first distance being different than the second distance.

109. (Previously presented) The method of claim 37, further comprising:
at least partially immersing the microelectronic substrate in a liquid electrolyte;
moving portions of the electrically conductive material from the microelectronic substrate to the liquid electrolyte; and
removing the portions from the liquid electrolyte.

110. (Previously presented) The method of claim 37, further comprising:
disposing a first quantity of an electrolyte between the conductive material and the electrodes only in a first region of the microelectronic substrate immediately proximate to the electrodes;

moving the microelectronic substrate and/or the electrodes to align a second region of the microelectronic substrate with the electrodes; and

disposing a second quantity of the electrolyte between the conductive material and the electrodes only in the second region of the microelectronic substrate.

111. (Previously presented) The method of claim 37, further comprising:

disposing a first electrolyte adjacent to the first electrode;

disposing a second electrolyte different than the first electrolyte adjacent to the conductive material of the microelectronic substrate; and

at least restricting movement of the second electrolyte toward the first electrode.

112. (Previously presented) The method of claim 37, further comprising:

generating a signal corresponding to a rate at which the conductive material is removed from the microelectronic substrate and/or an amount of conductive material remaining on the microelectronic substrate; and

controlling an interaction between the microelectronic substrate and the electrodes based on the signal.

113. (Previously presented) The method of claim 37 wherein removing the conductive material includes contacting the microelectronic substrate with a polishing pad while moving at least one of the microelectronic substrate and the electrodes relative to the other.

114. (Previously presented) The method of claim 6 wherein removing the conductive material includes contacting the microelectronic substrate with a polishing pad while moving at least one of the microelectronic substrate and the electrodes relative to the other.

115. (Previously presented) The method of claim 8 wherein removing the conductive material includes contacting the microelectronic substrate with a polishing

pad while moving at least one of the microelectronic substrate and the electrodes relative to the other.

116. (Cancelled)

117. (Previously presented) The method of claim 43 wherein removing the conductive material includes contacting the microelectronic substrate with a polishing pad while moving at least one of the microelectronic substrate and the electrodes relative to the other.

118. (Previously presented) The apparatus of claim 53, further comprising a polishing pad support positioned to carry a polishing pad in contact with the microelectronic substrate.

119. (Previously presented) The apparatus of claim 55, further comprising a polishing pad support positioned to carry a polishing pad in contact with the microelectronic substrate.

120. (Previously presented) The apparatus of claim 76, further comprising a polishing pad support positioned to carry a polishing pad in contact with the microelectronic substrate.

121. (Previously presented) The apparatus of claim 94, further comprising a polishing pad support positioned to carry a polishing pad in contact with the microelectronic substrate.

122. (Previously presented) The apparatus of claim 95, further comprising a polishing pad support positioned to carry a polishing pad in contact with the microelectronic substrate.

123. (Previously presented) The apparatus of claim 98, further comprising a polishing pad support positioned to carry a polishing pad in contact with the microelectronic substrate.

124. (Previously presented) The apparatus of claim 99, further comprising a polishing pad support positioned to carry a polishing pad in contact with the microelectronic substrate.